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Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	PIC
Core Size	8-Bit
Speed	4MHz
Connectivity	UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	1.75KB (1K x 14)
Program Memory Type	FLASH
EEPROM Size	128 x 8
RAM Size	224 x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-SSOP (0.209", 5.30mm Width)
Supplier Device Package	20-SSOP
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic16lf627-04i-ss

## 2.1 Clocking Scheme/Instruction Cycle

The clock input (OSC1/CLKIN/RA7 pin) is internally divided by four to generate four non-overlapping quadrature clocks namely Q1, Q2, Q3 and Q4. Internally, the program counter (PC) is incremented every Q1, the instruction is fetched from the program memory and latched into the instruction register in Q4. The instruction is decoded and executed during the following Q1 through Q4. The clocks and instruction execution flow is shown in Figure 2-2.

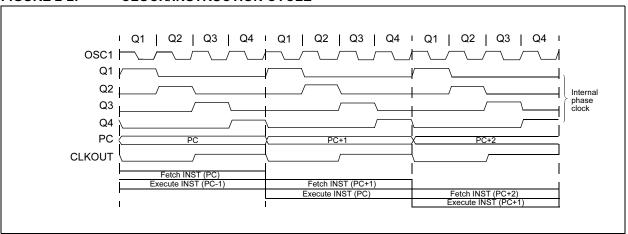
#### 2.2 Instruction Flow/Pipelining

An "Instruction Cycle" consists of four Q cycles (Q1, Q2, Q3 and Q4). The instruction fetch and execute are pipelined such that fetch takes one instruction cycle while decode and execute takes another instruction cycle. However, due to the pipelining, each instruction effectively executes in one cycle. If an instruction causes the program counter to change, (e.g., GOTO) then two cycles are required to complete the instruction (Example 2-1).

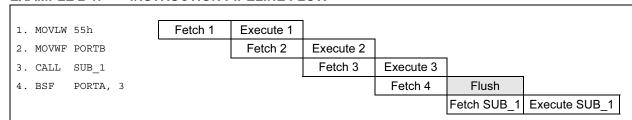
A fetch cycle begins with the program counter (PC) incrementing in Q1.

In the execution cycle, the fetched instruction is latched into the "Instruction Register (IR)" in cycle Q1. This instruction is then decoded and executed during the Q2, Q3, and Q4 cycles. Data memory is read during Q2 (operand read) and written during Q4 (destination write).

FIGURE 2-2: CLOCK/INSTRUCTION CYCLE



#### **EXAMPLE 2-1: INSTRUCTION PIPELINE FLOW**



All instructions are single cycle, except for any program branches. These take two cycles since the fetch instruction is "flushed" from the pipeline while the new instruction is being fetched and then executed.

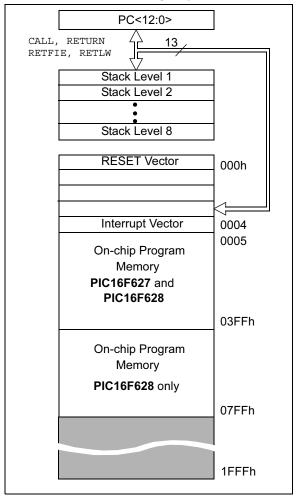
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#### 3.0 MEMORY ORGANIZATION

#### 3.1 Program Memory Organization

The PIC16F62X has a 13-bit program counter capable of addressing an 8K x 14 program memory space. Only the first 1K x 14 (0000h - 03FFh) for the PIC16F627 and 2K x 14 (0000h - 07FFh) for the PIC16F628 are physically implemented. Accessing a location above these boundaries will cause a wrap-around within the first 1K x 14 space (PIC16F627) or 2K x 14 space (PIC16F628). The RESET vector is at 0000h and the interrupt vector is at 0004h (Figure 3-1).

FIGURE 3-1: PROGRAM MEMORY MAP AND STACK



#### 3.2 Data Memory Organization

The data memory (Figure 3-2) is partitioned into four banks, which contain the general purpose registers and the Special Function Registers (SFR). The SFR's are located in the first 32 locations of each Bank. Register locations 20-7Fh, A0h-FFh, 120h-14Fh, 170h-17Fh and 1F0h-1FFh are general purpose registers implemented as static RAM.

The Table below lists how to access the four banks of registers:

	RP1	RP0
Bank0	0	0
Bank1	0	1
Bank2	1	0
Bank3	1	1

Addresses F0h-FFh, 170h-17Fh and 1F0h-1FFh are implemented as common RAM and mapped back to addresses 70h-7Fh.

## 3.2.1 GENERAL PURPOSE REGISTER FILE

The register file is organized as 224 x 8 in the PIC16F62X. Each is accessed either directly or indirectly through the File Select Register FSR (See Section 3.4).

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#### 3.2.2.1 STATUS Register

The STATUS register, shown in Register 3-1, contains the arithmetic status of the ALU, the RESET status and the bank select bits for data memory (SRAM).

The STATUS register can be the destination for any instruction, like any other register. If the STATUS register is the destination for an instruction that affects the Z, DC or C bits, then the write to these three bits is disabled. These bits are set or cleared according to the device logic. Furthermore, the  $\overline{\text{TO}}$  and  $\overline{\text{PD}}$  bits are not writable. Therefore, the result of an instruction with the STATUS register as destination may be different than intended.

For example, CLRF STATUS will clear the upper-three bits and set the Z bit. This leaves the STATUS register as 000uu1uu (where u = unchanged).

It is recommended, therefore, that only BCF, BSF, SWAPF and MOVWF instructions are used to alter the STATUS register because these instructions do not affect any STATUS bit. For other instructions, not affecting any STATUS bits, see the "Instruction Set Summary".

Note 1: The C and DC bits operate as a Borrow and Digit Borrow out bit, respectively, in subtraction. See the SUBLW and SUBWF instructions for examples.

#### REGISTER 3-1: STATUS REGISTER (ADDRESS: 03h, 83h, 103h, 183h)

R/W-0	R/W-0	R/W-0	R-1	R-1	R/W-x	R/W-x	R/W-x
IRP	RP1	RP0	TO	PD	Z	DC	С
bit 7							bit 0

bit 7 IRP: Register Bank Select bit (used for indirect addressing)

1 = Bank 2, 3 (100h - 1FFh)

0 = Bank 0, 1 (00h - FFh)

bit 6-5 RP1:RP0: Register Bank Select bits (used for direct addressing)

00 = Bank 0 (00h - 7Fh)

01 = Bank 1 (80h - FFh)

10 = Bank 2 (100h - 17Fh)

11 = Bank 3 (180h - 1FFh)

bit 4 **TO**: Timeout bit

1 = After power-up, CLRWDT instruction, or SLEEP instruction

0 = A WDT timeout occurred

bit 3 **PD**: Power-down bit

1 = After power-up or by the CLRWDT instruction

0 = By execution of the SLEEP instruction

bit 2 **Z**: Zero bit

1 = The result of an arithmetic or logic operation is zero

0 = The result of an arithmetic or logic operation is not zero

bit 1 DC: Digit carry/borrow bit (ADDWF, ADDLW, SUBLW, SUBWF instructions) (for borrow the polarity is reversed)

1 = A carry-out from the 4th low order bit of the result occurred

0 = No carry-out from the 4th low order bit of the result

bit 0 C: Carry/borrow bit (ADDWF, ADDLW, SUBLW, SUBWF instructions)

1 = A carry-out from the Most Significant bit of the result occurred

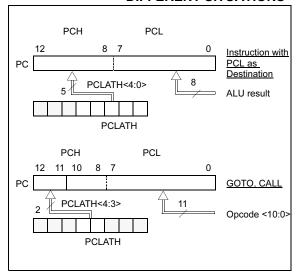
0 = No carry-out from the Most Significant bit of the result occurred

**Note 1:** For borrow the polarity is reversed. A subtraction is executed by adding the two's complement of the second operand. For rotate (RRF, RLF) instructions, this bit is loaded with either the high or low order bit of the source register.

#### 3.3 PCL and PCLATH

The program counter (PC) is 13-bits wide. The low byte comes from the PCL register, which is a readable and writable register. The high byte (PC<12:8>) is not directly readable or writable and comes from PCLATH. On any RESET, the PC is cleared. Figure 3-3 shows the two situations for the loading of the PC. The upper example in the figure shows how the PC is loaded on a write to PCL (PCLATH<4:0>  $\rightarrow$  PCH). The lower example in the figure shows how the PC is loaded during a CALL or GOTO instruction (PCLATH<4:3>  $\rightarrow$  PCH).

FIGURE 3-3: LOADING OF PC IN DIFFERENT SITUATIONS



#### 3.3.1 COMPUTED GOTO

A computed GOTO is accomplished by adding an offset to the program counter (ADDWF PCL). When doing a table read using a computed GOTO method, care should be exercised if the table location crosses a PCL memory boundary (each 256 byte block). Refer to the application note "Implementing a Table Read" (AN556).

#### 3.3.2 STACK

The PIC16F62X family has an 8-level deep x 13-bit wide hardware stack (Figure 3-1 and Figure 3-2). The stack space is not part of either program or data space and the stack pointer is not readable or writable. The PC is PUSHed onto the stack when a CALL instruction is executed or an interrupt causes a branch. The stack is POPed in the event of a RETURN, RETLW or a RETFIE instruction execution. PCLATH is not affected by a PUSH or POP operation.

The stack operates as a circular buffer. This means that after the stack has been PUSHed eight times, the ninth push overwrites the value that was stored from the first push. The tenth push overwrites the second push (and so on).

- Note 1: There are no STATUS bits to indicate stack overflow or stack underflow conditions.
  - 2: There are no instructions/mnemonics called PUSH or POP. These are actions that occur from the execution of the CALL, RETURN, RETLW and RETFIE instructions, or the vectoring to an interrupt address.

## 3.4 Indirect Addressing, INDF and FSR Registers

The INDF register is not a physical register. Addressing the INDF register will cause indirect addressing.

Indirect addressing is possible by using the INDF register. Any instruction using the INDF register actually accesses data pointed to by the file select register (FSR). Reading INDF itself indirectly will produce 00h. Writing to the INDF register indirectly results in a nooperation (although STATUS bits may be affected). An effective 9-bit address is obtained by concatenating the 8-bit FSR register and the IRP bit (STATUS<7>), as shown in Figure 3-4.

A simple program to clear RAM location 20h-2Fh using indirect addressing is shown in Example 3-1.

#### **EXAMPLE 3-1:** Indirect Addressing

	movlw	0x20	;initialize pointer
	movwf	FSR	;to RAM
NEXT	clrf	INDF	clear INDF register;
	incf	FSR	;inc pointer
	btfss	FSR,4	;all done?
	goto	NEXT	;no clear next
			;yes continue

FIGURE 5-1: BLOCK DIAGRAM OF RA0/AN0:RA1/AN1 PINS

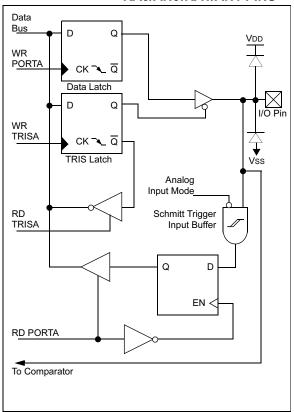
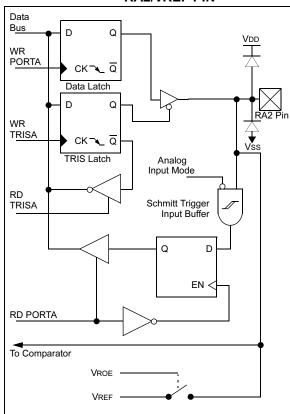
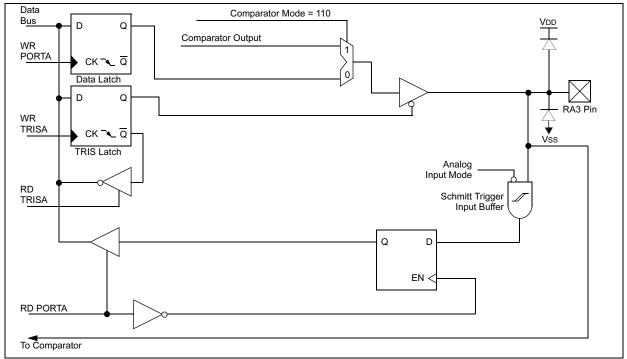


FIGURE 5-2: BLOCK DIAGRAM OF RA2/VREF PIN



#### FIGURE 5-3: BLOCK DIAGRAM OF THE RA3/AN3 PIN



<u>V</u>DD RBPU \_d ℙ weak pull-up TMR1 oscillator To RB6 Data Bus D Q WR PORTB RB7/T1OSI •ck <del>√</del>Q pin Data Latch ↓ Vss D Q WR TRISB ск ∕\_ а TRIS Latch **RD TRISB** T10SCEN  $\mathsf{TTL}$ RD PORTB input buffer Serial programming input Schmitt Trigger Q D EN< Set RBIF From other Q D RB<7:4> pins EN<

FIGURE 5-15: BLOCK DIAGRAM OF THE RB7/T10SI PIN

#### 9.0 COMPARATOR MODULE

The Comparator module contains two analog comparators. The inputs to the comparators are multiplexed with the RA0 through RA3 pins. The Onchip Voltage Reference (Section 10.0) can also be an input to the comparators.

The CMCON register, shown in Register 9-1, controls the comparator input and output multiplexers. A block diagram of the comparator is shown in Figure 9-1.

#### REGISTER 9-1: CMCON REGISTER (ADDRESS: 01Fh)

R-0	R-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0	R/W-0
C2OUT	C10UT	C2INV	C1INV	CIS	CM2	CM1	CM0
bit 7							bit 0

bit 7 C2OUT: Comparator 2 Output

When C2INV = 0: 1 = C2 VIN+ > C2 VIN-0 = C2 VIN+ < C2 VIN-

When C2INV = 1:

1 = C2 VIN+ < C2 VIN-0 = C2 VIN+ > C2 VIN-

bit 6 C10UT: Comparator 1 Output

When C1INV = 0: 1 = C1 VIN+ > C1 VIN-0 = C1 VIN+ < C1 VIN-

When C1INV = 1:

1 = C1 Vin+ < C1 Vin-0 = C1 Vin+ > C1 Vin-

bit 5 C2INV: Comparator 2 Output Inversion

1 = C2 Output inverted0 = C2 Output not inverted

bit 4 C1INV: Comparator 1 Output Inversion

1 = C1 Output inverted0 = C1 Output not inverted

bit 3 CIS: Comparator Input Switch

When CM2:CM0: = 001

Then:

 $_1$  = C1 Vin- connects to RA3

0 = C1 Vin- connects to RA0

When CM2:CM0 = 010

Then:

1 = C1 Vin- connects to RA3

C2 VIN- connects to RA2

0 = C1 Vin- connects to RA0

C2 VIN- connects to RA1

bit 2-0 CM2:CM0: Comparator Mode

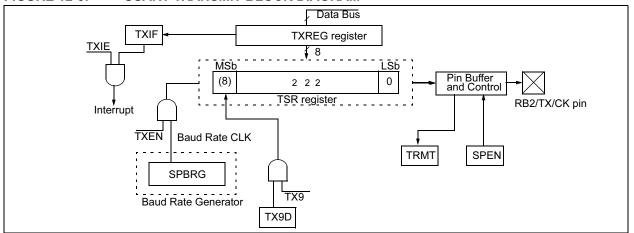
Figure 9-1 shows the Comparator modes and CM2:CM0 bit settings

Legend:

R = Readable bit W = Writable bit U = Unimplemented bit, read as '0'

-n = Value at POR '1' = Bit is set '0' = Bit is cleared x = Bit is unknown

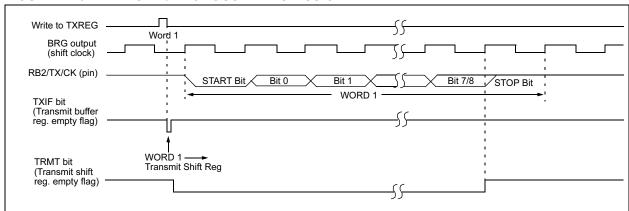
#### FIGURE 12-5: USART TRANSMIT BLOCK DIAGRAM



Steps to follow when setting up an Asynchronous Transmission:

- Initialize the SPBRG register for the appropriate baud rate. If a high speed baud rate is desired, set bit BRGH. (Section 12.1)
- 2. Enable the asynchronous serial port by clearing bit SYNC and setting bit SPEN.
- If interrupts are desired, then set enable bit TXIE.
- 4. If 9-bit transmission is desired, then set transmit bit TX9.
- Enable the transmission by setting bit TXEN, which will also set bit TXIF.
- 6. If 9-bit transmission is selected, the ninth bit should be loaded in bit TX9D.
- 7. Load data to the TXREG register (starts transmission).

#### FIGURE 12-6: ASYNCHRONOUS TRANSMISSION



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## PIC16F62X

NOTES:

## 13.3 READING THE EEPROM DATA MEMORY

To read a data memory location, the user must write the address to the EEADR register and then set control bit RD (EECON1<0>). The data is available, in the very next cycle, in the EEDATA register; therefore it can be read in the next instruction. EEDATA will hold this value until another read or until it is written to by the user (during a write operation).

#### **EXAMPLE 13-1: DATA EEPROM READ**

```
BSF STATUS, RPO ; Bank 1

MOVLW CONFIG_ADDR ;

MOVWF EEADR ; Address to read

BSF EECON1, RD ; EE Read

MOVF EEDATA, W ; W = EEDATA

BCF STATUS, RPO ; Bank 0
```

## 13.4 WRITING TO THE EEPROM DATA MEMORY

To write an EEPROM data location, the user must first write the address to the EEADR register and the data to the EEDATA register. Then the user must follow a specific sequence to initiate the write for each byte.

#### **EXAMPLE 13-2: DATA EEPROM WRITE**

```
STATUS, RP0
       BSF
                                : Bank 1
      BSF
               EECON1, WREN
                                ; Enable write
       BCF
               INTCON, GIE
                                ; Disable INTs.
      MOVLW
               55h
Required
Sequence
      MOVWF
               EECON2
                                ; Write 55h
      MOVI.W
               AAh
                                ; Write AAh
      MOVWF
               EECON2
       BSF
               EECON1,WR
                                ; Set WR bit
                                ; begin write
       BSF
               INTCON, GIE
                                ; Enable INTs.
```

The write will not initiate if the above sequence is not exactly followed (write 55h to EECON2, write AAh to EECON2, then set WR bit) for each byte. We strongly recommend that interrupts be disabled during this code segment. A cycle count is executed during the required sequence. Any number that is not equal to the required cycles to execute the required sequence will cause the data not to be written into the EEPROM.

Additionally, the WREN bit in EECON1 must be set to enable write. This mechanism prevents accidental writes to data EEPROM due to errant (unexpected) code execution (i.e., lost programs). The user should keep the WREN bit clear at all times, except when updating EEPROM. The WREN bit is not cleared by hardware.

After a write sequence has been initiated, clearing the WREN bit will not affect this write cycle. The WR bit will be inhibited from being set unless the WREN bit is set.

At the completion of the write cycle, the WR bit is cleared in hardware and the EE Write Complete Interrupt Flag bit (EEIF) is set. The user can either enable this interrupt or poll this bit. The EEIF bit in the PIR1 registers must be cleared by software.

#### 13.5 WRITE VERIFY

Depending on the application, good programming practice may dictate that the value written to the Data EEPROM should be verified (Example 13-3) to the desired value to be written. This should be used in applications where an EEPROM bit will be stressed near the specification limit.

#### **EXAMPLE 13-3: WRITE VERIFY**

```
BSF
         STATUS, RPO ; Bank 1
   MOVF
         EEDATA, W
   BSF
         EECON1, RD
                      ; Read the
                      ; value written
; Is the value written (in W reg) and
; read (in EEDATA) the same?
   SUBWF EEDATA, W
   BCF STATUS, RPO ; BankO
   BTFSS STATUS, Z
                      ; Is difference 0?
   GOTO WRITE_ERR
                      ; NO, Write error
                      ; YES, Good write
                      ; Continue program
```

## 13.6 PROTECTION AGAINST SPURIOUS WRITE

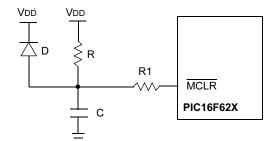
There are conditions when the device may not want to write to the data EEPROM memory. To protect against spurious EEPROM writes, various mechanisms have been built in. On power-up, WREN is cleared. Also, the Power-up Timer (72 ms duration) prevents EEPROM write.

The write initiate sequence, and the WREN bit together help prevent an accidental write during brown-out, power glitch, or software malfunction.

## 13.7 DATA EEPROM OPERATION DURING CODE PROTECT

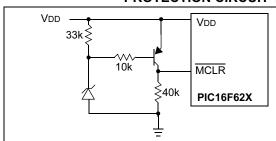
When the device is code protected, the CPU is able to read and write unscrambled data to the Data EEPROM.

# FIGURE 14-11: EXTERNAL POWER-ON RESET CIRCUIT (FOR SLOW VDD POWER-UP)



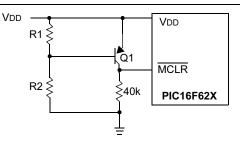
- Note 1: External Power-on Reset circuit is required only if VDD power-up slope is too slow. The diode D helps discharge the capacitor quickly when VDD powers down.
  - 2:  $R < 40 \text{ k}\Omega$  is recommended to make sure that voltage drop across R does not violate the device's electrical specification.
  - 3: R1 =  $100\Omega$  to  $1 \text{ k}\Omega$  will limit any current flowing into  $\overline{\text{MCLR}}$  from external capacitor C in the event of  $\overline{\text{MCLR}}$ /VPP pin breakdown due to Electrostatic Discharge (ESD) or Electrical Overstress (EOS).

## FIGURE 14-12: EXTERNAL BROWN-OUT PROTECTION CIRCUIT 1



- Note 1: This circuit will activate RESET when VDD goes below (Vz + 0.7V) where Vz = Zener voltage.
  - 2: Internal Brown-out Detect Reset circuitry should be disabled when using this circuit.

## FIGURE 14-13: EXTERNAL BROWN-OUT PROTECTION CIRCUIT 2



Note 1: This Brown-out Circuit is less expensive, albeit less accurate. Transistor Q1 turns off when VDD is below a certain level such that:

$$V_{DD} \times \frac{R1}{R1 + R2} = 0.7V$$

- 2: Internal Brown-out Detect Reset should be disabled when using this circuit.
- Resistors should be adjusted for the characteristics of the transistor.

#### 14.6.1 RB0/INT INTERRUPT

External interrupt on RB0/INT pin is edge triggered: either rising if INTEDG bit (OPTION<6>) is set, or falling, if INTEDG bit is clear. When a valid edge appears on the RB0/INT pin, the INTF bit (INTCON<1>) is set. This interrupt can be disabled by clearing the INTE control bit (INTCON<4>). The INTF bit must be cleared in software in the interrupt service routine before re-enabling this interrupt. The RB0/INT interrupt can wake-up the processor from SLEEP, if the INTE bit was set prior to going into SLEEP. The status of the GIE bit decides whether or not the processor branches to the interrupt vector following wake-up. See Section 14.9 for details on SLEEP, and Figure 14-17 for timing of wake-up from SLEEP through RB0/INT interrupt.

#### 14.6.2 TMR0 INTERRUPT

An overflow (FFh  $\rightarrow$  00h) in the TMR0 register will set the T0IF (INTCON<2>) bit. The interrupt can be enabled/disabled by setting/clearing T0IE (INTCON<5>) bit. For operation of the Timer0 module, see Section 6.0.

#### 14.6.3 PORTB INTERRUPT

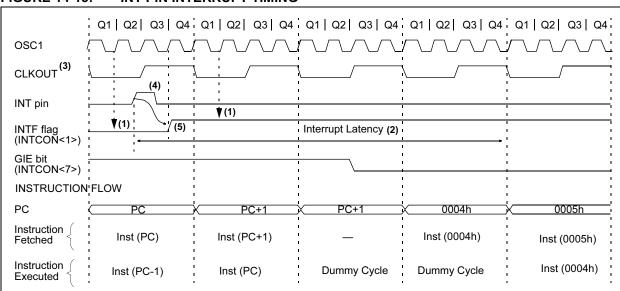
An input change on PORTB <7:4> sets the RBIF (INTCON<0>) bit. The interrupt can be enabled/disabled by setting/clearing the RBIE (INTCON<4>) bit. For operation of PORTB (Section 5.2).

Note: If a change on the I/O pin should occur when the read operation is being executed (start of the Q2 cycle), then the RBIF interrupt flag may not get set.

#### 14.6.4 COMPARATOR INTERRUPT

See Section 9.6 for complete description of comparator interrupts.

#### FIGURE 14-15: INT PIN INTERRUPT TIMING



- Note 1: INTF flag is sampled here (every Q1).
  - 2: Asynchronous interrupt latency = 3-4 Tcy. Synchronous latency = 3 Tcy, where Tcy = instruction cycle time. Latency is the same whether Inst (PC) is a single cycle or a 2-cycle instruction.
  - 3: CLKOUT is available in ER and INTRC Oscillator mode.
  - 4: For minimum width of INT pulse, refer to AC specs.
  - 5: INTF is enabled to be set anytime during the Q4-Q1 cycles.

RRF	Rotate Right f through Carry	SUBLW	Subtract W from Literal
Syntax:	[label] RRF f,d	Syntax:	[ label ] SUBLW k
Operands:	$0 \leq f \leq 127$	Operands:	$0 \leq k \leq 255$
	$d \in [0,1]$	Operation:	$k - (W) \rightarrow (W)$
Operation:	See description below	Status	C, DC, Z
Status Affected:	С	Affected:	
Encoding:	00 1100 dfff ffff	Encoding:	11 110x kkkk kkkk
Description:	The contents of register 'f' are	Description:	The W register is subtracted (2's
	rotated one bit to the right		complement method) from the eight
	through the Carry Flag. If 'd' is 0 the result is placed in the W		bit literal 'k'. The result is placed in the W register.
	register. If 'd' is 1 the result is	Words:	1
	placed back in register 'f'.	Cycles:	1
	C REGISTER F	Example 1:	SUBLW 0x02
Words:	1	Zampio II	Before Instruction
	·		W = 1
Cycles:	1		C = ?
Example	RRF REG1, 0		After Instruction
	Before Instruction REG1 = 1110 0110		W = 1
	C = 0		C = 1; result is positive
	After Instruction	Example 2:	Before Instruction
	REG1 = 1110 0110 W = 0111 0011		W = 2
	C = 0		C = ?
			After Instruction
01.550			W = 0
SLEEP			C = 1; result is zero
Syntax:	[ label ] SLEEP	Example 3:	Before Instruction
Operands:	None		W = 3 C = ?
Operation:	$00h \to WDT,$		After Instruction
	0 → <u>WD</u> T prescaler, 1 → <del>TO</del> ,		
	$0 \rightarrow \overline{PD}$		W = 0xFF C = 0; result is negative
Status Affected:	TO, PD		,
Encoding:	00 0000 0110 0011		
Description:	The power-down STATUS bit,		
•	PD is cleared. Timeout		
	STATUS bit, TO is set. Watchdog Timer and its		
	prescaler are cleared.		
	The processor is put into		
	SLEEP mode with the oscillator stopped. See		
	Section 14.9 for more details.		
Words:	1		
Cycles:	1		
Example:	SLEEP		
r ·			

Note: The graphs and tables provided in this section are for design guidance and are not tested.

FIGURE 18-2: MAXIMUM IDD VS FOSC OVER VDD (HS MODE)

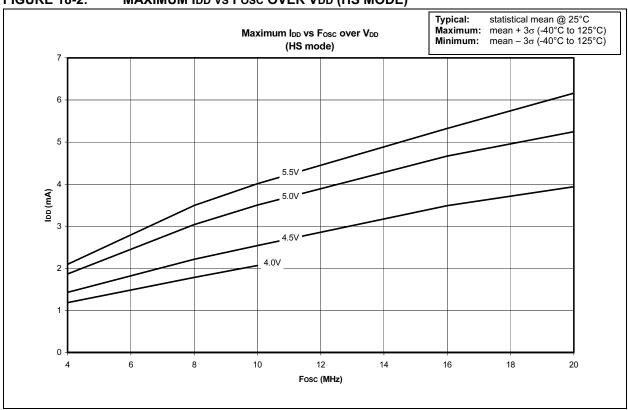
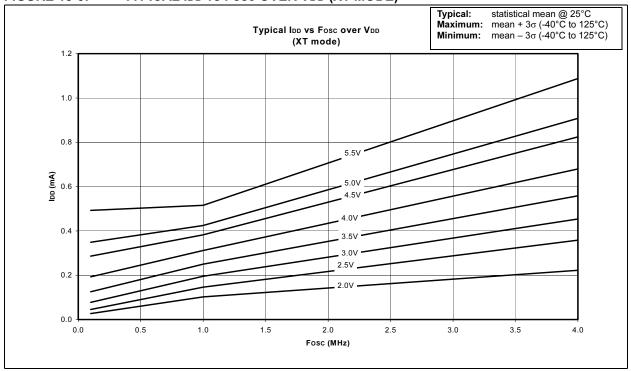


FIGURE 18-3: TYPICAL IDD VS FOSC OVER VDD (XT MODE)



Note: The graphs and tables provided in this section are for design guidance and are not tested.

FIGURE 18-24: MAXIMUM IDD VS VDD OVER TEMPERATURE (-40 TO +125°C) INTERNAL 37 kHz OSCILLATOR

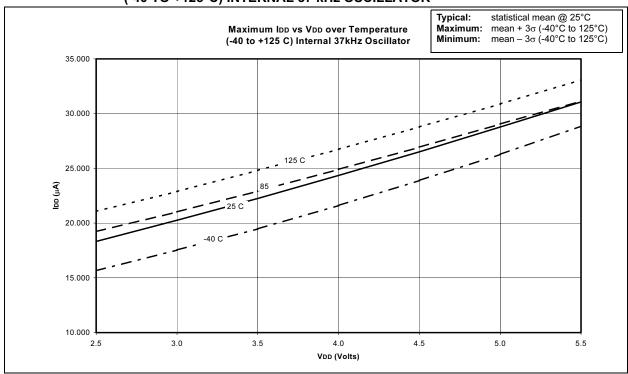
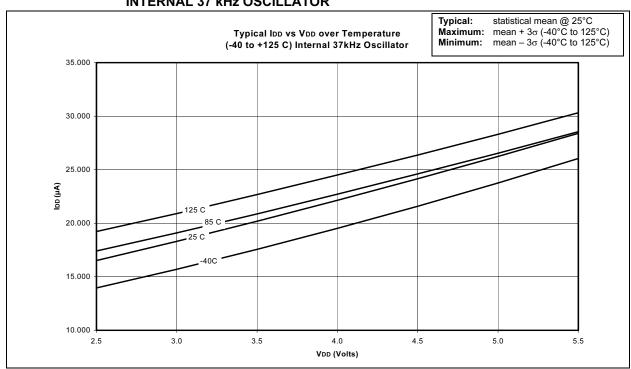
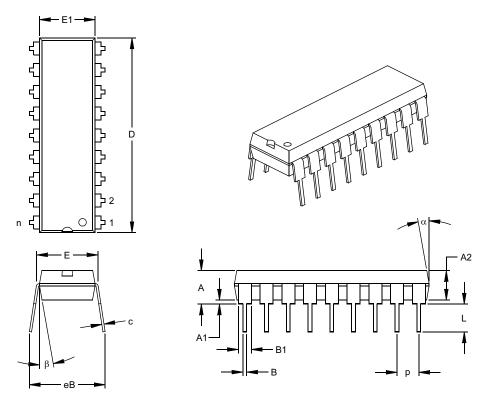


FIGURE 18-25: TYPICAL IDD VS VDD OVER TEMPERATURE (-40 TO +125°C) INTERNAL 37 kHz OSCILLATOR



### K04-007 18-Lead Plastic Dual In-line (P) - 300 mil



	Units		INCHES*			MILLIMETERS		
Dimensi	on Limits	MIN	NOM	MAX	MIN	NOM	MAX	
Number of Pins	n		18			18		
Pitch	р		.100			2.54		
Top to Seating Plane	Α	.140	.155	.170	3.56	3.94	4.32	
Molded Package Thickness	A2	.115	.130	.145	2.92	3.30	3.68	
Base to Seating Plane	A1	.015			0.38			
Shoulder to Shoulder Width	Е	.300	.313	.325	7.62	7.94	8.26	
Molded Package Width	E1	.240	.250	.260	6.10	6.35	6.60	
Overall Length	D	.890	.898	.905	22.61	22.80	22.99	
Tip to Seating Plane	L	.125	.130	.135	3.18	3.30	3.43	
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38	
Upper Lead Width	B1	.045	.058	.070	1.14	1.46	1.78	
Lower Lead Width	В	.014	.018	.022	0.36	0.46	0.56	
Overall Row Spacing §	eB	.310	.370	.430	7.87	9.40	10.92	
Mold Draft Angle Top	α	5	10	15	5	10	15	
Mold Draft Angle Bottom	β	5	10	15	5	10	15	

Notes:

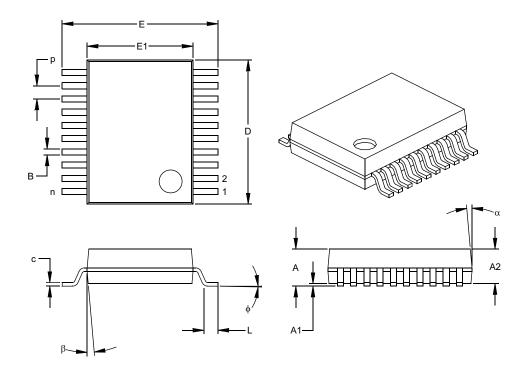
Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" (0.254mm) per side.

JEDEC Equivalent: MS-001

Drawing No. C04-007

<sup>\*</sup> Controlling Parameter § Significant Characteristic

### K04-072 20-Lead Plastic Shrink Small Outline (SS) - 5.30 mm



	Units	INCHES*			N	11LLIMETERS	6
Dimension	Limits	MIN	NOM	MAX	MIN	NOM	MAX
Number of Pins	n		20			20	
Pitch	р		.026			0.65	
Overall Height	Α	.068	.073	.078	1.73	1.85	1.98
Molded Package Thickness	A2	.064	.068	.072	1.63	1.73	1.83
Standoff §	A1	.002	.006	.010	0.05	0.15	0.25
Overall Width	E	.299	.309	.322	7.59	7.85	8.18
Molded Package Width	E1	.201	.207	.212	5.11	5.25	5.38
Overall Length	D	.278	.284	.289	7.06	7.20	7.34
Foot Length	L	.022	.030	.037	0.56	0.75	0.94
Lead Thickness	С	.004	.007	.010	0.10	0.18	0.25
Foot Angle	ф	0	4	8	0.00	101.60	203.20
Lead Width	В	.010	.013	.015	0.25	0.32	0.38
Mold Draft Angle Top	α	0	5	10	0	5	10
Mold Draft Angle Bottom	β	0	5	10	0	5	10

Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed

.010" (0.254mm) per side.
JEDEC Equivalent: MO-150
Drawing No. C04-072

<sup>\*</sup> Controlling Parameter § Significant Characteristic

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